



5082-3080

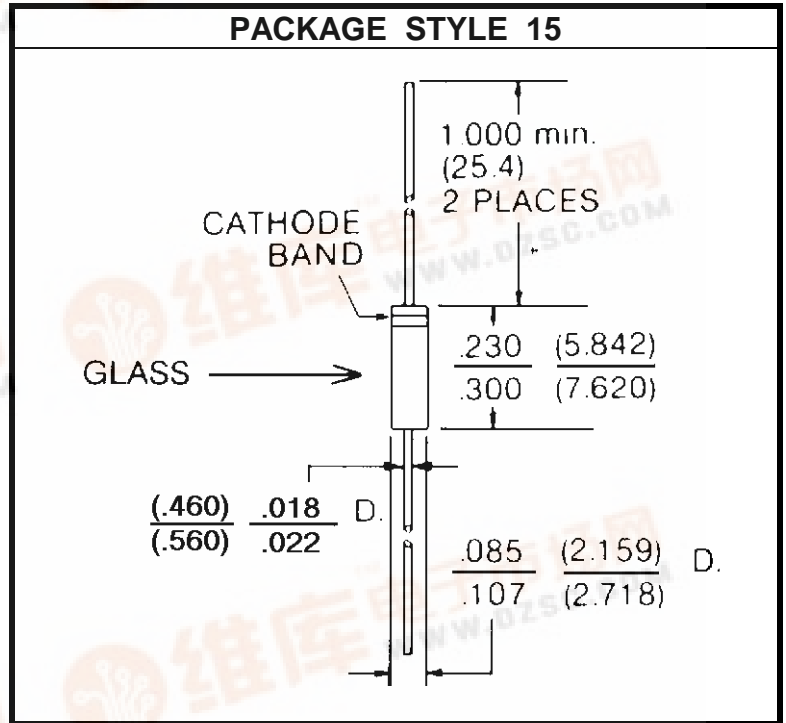
SILICON PIN DIODE

DESCRIPTION:

The **ASI 5082-3080** PIN Diode is Designed for Low Power RF Switching and Attenuating Applications.

MAXIMUM RATINGS

I	250 mA
V	100 V
P_{DISS}	250 mW @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
T_{SOLD}	260 °C for 5 sec.



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V _R	I _R = 10 μA	100			V
V _F	I _F = 100 mA		1.0		V
τ	I _F = 50 mA I _R = 250 mA		1300		μS
R _S	I _F = 100 mA f = 100 MHz			2.5	Ω
C _t	V _R = 50 V f = 1.0 MHz			0.4	pF
R _H	I _F = 10 μA f = 100 MHz	1000			Ω
R _L	I _F = 20 mA f = 100 MHz			8.0	Ω

